

CONTENT ADDRESSABLE MEMORY WITH PFET PASSGATE SRAM CELLS

Abstract of the Disclosure

A Content Addressable Memory (CAM) cell with PFET passgate SRAM cells which results in a smaller cell size because of the more balanced number of 8 PFET devices and 8 NFET devices. The PFET passgates allow the size of the SRAM cell pulldown devices to be reduced, and lower the power dissipation in the SRAM during standby or during read/write.

Figures